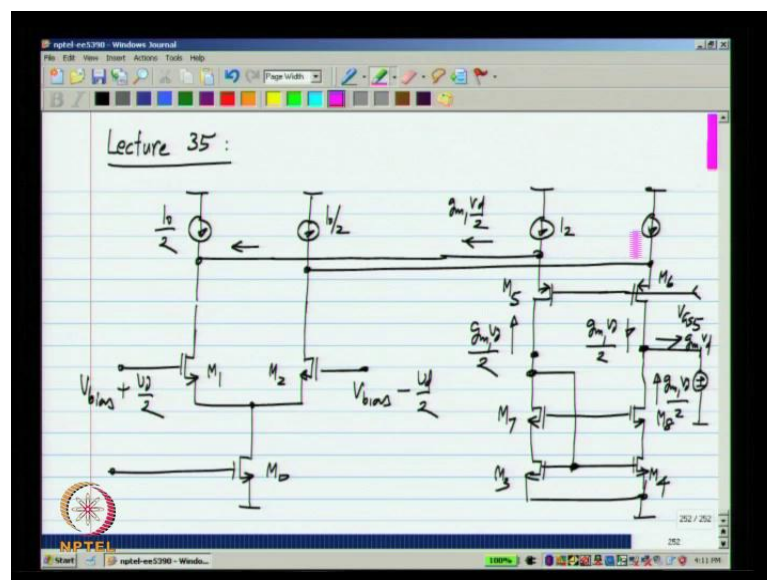


Analog Integrated Circuit Design
Prof. Nagendra Krishnapura
Department of Electrical Engineering
Indian Institute of Technology, Madras

Lecture - 35
Folded Cascode Opamp

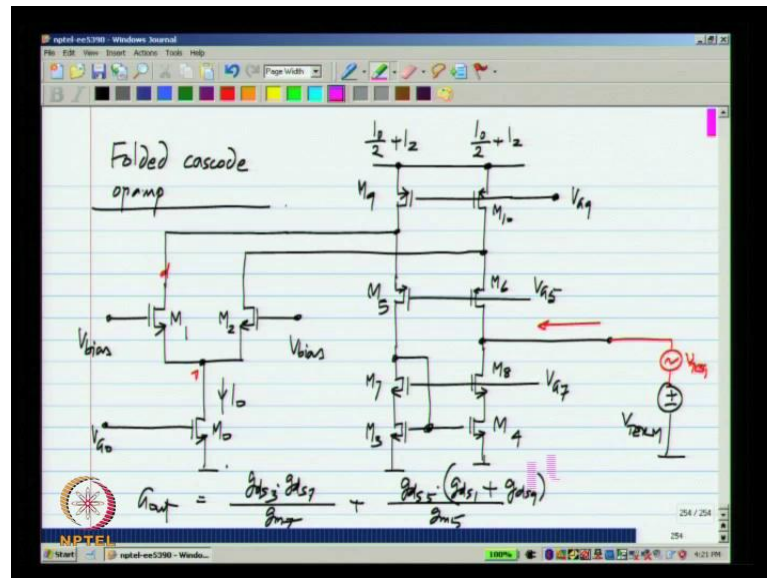
Hello and welcome to lecture 35 of Analog Integrated Circuit Design, in the previous lecture we analyze the telescopic cascode opamp in great detail. Also we came up with a different topology by using a p MOS cascode device, or p MOS common gate amplifier with M MOS differential pair, we had this topology, which first called the folded cascode opamp, in this lecture we analyze this in detail.

(Refer Slide Time: 00:43)



This is the circuit we have the M MOS differential pair followed by a p MOS cascode device, and in n MOS current mirror to take the current from this side and combine it, and given output of $g_m v_d$, where v_d is the differential input. Now, you see that the bias sources I_1 and I_2 used to subtract the current from M_1 , and the bias sources I_1 and I_2 of these cascode devices are in parallel, so they will be combine into a single source and implemented with MOS transistors.

(Refer Slide Time: 01:25)



I will draw the circuit including that modification, these are current source devices, these are the cascode devices M 1, M 2, M 5, M 6, M 0, and we have the M MOS cascode current mirror. The gate voltage is some bias voltage generate from a p MOS current mirror, it could be something other ((Refer Time: 03:18)) I will not show it here, but that is how it is generate.

Similarly, V G 0 is generated in the same way, so this forms current source I 0 and M 9 and M 10 implement a current source of I naught by 2 plus I 2, the output is taken from here. It can be loaded by a capacitor, if you are implementing an opamp or it could be loaded by just a voltage source, when we are testing it as a trans conductor by monitoring the output current, and these are fixed bias voltages to bias the common gate amplifier.

So, this were folded cascode opamp, now compare to the telescopic cascode opamp, we have these two extra devices M 9 and M 10, in the telescopic cascode opamp everything was tacked on top of each other. And we did not need these extra sources for biasing, but now we do, we have to see what the effect of those things are, because of we are already analyze the cascode opamp in detail. I will not going into every detail of this particular opamp, I will only analyze those aspects, which are different from this compared to the telescopic cascode.

So, first of all let me draw the quiescent currents, write down the quiescent currents here, in the two arms it will be I naught by 2 and I naught by 2, and in M 5 and M 6 and these

other transistors. It will be I_2 and I_2 , now if I apply an incremental voltage, v_{d2} and minus v_{d2} to the differential pair, a current in M_1 increases by $g_{m1} v_{d2}$ this voltage is almost at 0, v_1 with this symmetrical loads. As, we analyze it earlier, and this is at minus $g_{m1} v_{d2}$, now if you work it out you will see that in this transistor in M_6 , we will have I_2 plus $g_{m1} v_{d2}$ that comes from Kirchhoff law this node.

And similarly, in M_5 will have I_2 minus $g_{m1} v_{d2}$, and it also gets mirrored in M_4 and M_8 , so finally here we will have I_2 minus $g_{m1} v_{d2}$ and I_{out} as we knew was simply g_{m1} times v_d . Exactly, the same as before, so the trans conductance of the folded cascode opamp is also g_{m1} , it is simply the trans conductance of the input differential pair.

This is not very surprising, because all we have done is to use current buffers with unity gain after the differential pair, now the important thing is the output conductance, because the high output conductance is the region we go to cascode topologies. Let me remove all of these, now by symmetry just like in the differential pair, and in the telescopic cascode opamp, the voltage here and there are the same in the quiescent condition.

Let me remove the load all together if the devices are exactly matched, the voltage on the drain of M_7 , and at the drain of M_8 will be exactly the same, you can assume them to be different, and come up with the contradiction as usual. And that is the voltage, with which we will terminate the trans conductor, let us say to this I had a test voltage, v_{test} and we have to find out, how much current will flow there. Now, it turns out that the situation is exactly the same as before, in fact the transistors are numbered, so that they are functionally identical to the similar number transistors.

M_1 and the M_2 are the differential pair, M_3 and M_4 are the main current mirror, M_5 and M_6 are the cascodes for the differential pair, M_7 and M_8 are the cascodes for the current mirror, we also have these extra transistors M_9 and M_{10} . Now, before what we had was that the contribution of the current source to the output conductance was simply the output conductance to the cascode source. So, we have g_{out} to be $g_{ds3} g_{ds7}$ by g_{m7} , that is the contribution due to this, and the contribution due to the differential pair

was g_{ds5} , g_{ds1} divided by g_{m5} , that is because the total conductance in the source of M_5 was contributed by the differential pair.

Now, to the addition to that we see that we have another transistors M_9 over here, so it turns out, that the output conductance due to the differential pair will also include the output conductance of these current source transistors M_9 and M_{10} . So, I will not analyze this please go add and do that, and you will find that this g_{ds9} simply adds to g_{ds1} , we have g_{ds1} looking this way. The actual situation is complicated, because of the asymmetric injection, and this way what we earlier, but the final result is that g_{ds1} will appear in parallel with g_{ds9} .

So, the total output conductance will be that much, the only difference is that, because of this extra current source transistors, we also have an additional output conductance, which will reduce the d c gain, so this is in fact a disadvantage.

(Refer Slide Time: 10:46)

Folded cascode transconductor / opamp

$$G_m = g_{m1}$$

$$G_{out} = \frac{g_{m7} g_{ds3}}{g_{m7}} + \frac{g_{ds5} (g_{ds1} + g_{ds9})}{g_{m5}}$$

Parasitic poles/zeros: $p_2 = -\frac{g_{m3}}{C_{d3}}$; $z_1 = -\frac{2g_{m3}}{C_{d3}}$; $\frac{g_{m5}}{C_{d1}}$

{ larger parasitic capacitances due to $M_9, 10$ }

We have the folded cascode trans conductor, and when it is loaded by capacitor c , it becomes a folded cascode opamp of unity gain frequency g_{m1} by c , so that the trans conductance of this is g_{m1} the output conductance is that one. Now, what about the frequency response, we see that the number of nodes in the circuit is exactly the same as before. And qualitatively they are also the same, except that there are these two transistors M_9 and M_{10} , so we will have parasitic capacitance at this node.

So, we will have this, which I have been calling $c d 3$, this causes a pole in the current mirror, so if you inject a current into this the output will be that current times 1 over 1 plus s by this pole. And the pole value we know is $g m 3$ by $c d 3$, and because it acts only one half of the current, the current from $M 1$, they also be a 0 at twice that frequency.

This is exactly the same as what was the case, with the simple differential pair opamp and also the telescopic cascode opamp, in addition to that we have $c d 1$, $c d 2$, and here I should call this $c s 7$ and $c s 8$. Each of these capacitors $c d 1$, $c d 2$, $c s 7$, $c s 8$ are at the input nodes of common gate amplifiers, and the input resistance of the common gate amplifier is simply 1 over $g m$ of the cascoding device.

So, each of these will create poles of value $g m 7$ by $c s 7$, $g m 8$ by $c s 8$, $g m 5$ by $c d 1$, $g m 6$ by $c d 2$, now there is an additional complication, because this particular pole $c s 7$ and $g m 7$ is inside this local feedback loop. And also all these poles from the lower side in the current mirror will act only onem half of the current they will act only the current from the $M 1$ not from $M 2$, so they will also create additional 0 's, they will have to be take into an account, it is just to comber some to calculate.

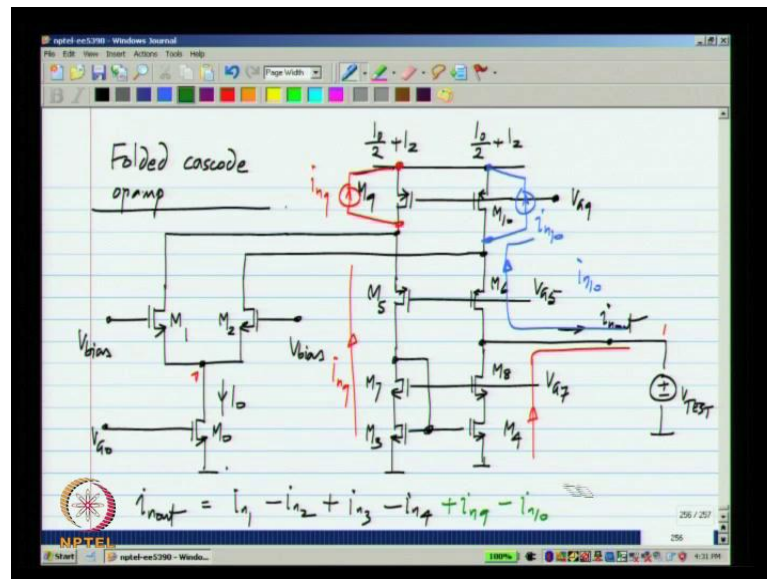
For now, we will just be satisfied with saying that there will be poles at these frequencies, and also some additional 0 's at similar frequency. Now, this pole at the source of $M 5$ and $M 6$ due to $c d 1$ and $c d 2$, they act on both the current from $M 1$, and the current from $M 2$. So, they will be pole of value $g M 5$ divided by $c d 1$ in the transfer function, so qualitatively the results are exactly the same as for the telescopic cascode opamp.

One difference is that because of these additional transistors we also get additional parasitic capacitances before $c d 1$ consisted of $c d b$ of $M 1$, $c s b$ of $M 5$, $c g s$ of $M 5$, now in addition to these we also have $c d b$ of $M 9$. So, while qualitatively it is the same the parasitic capacitance value will be higher, and so pole frequency will be at a lower value, also note that these transistors $M 9$ and $M 10$ carry large currents compare to $M 1$ $M 2$ or these other transistors.

So, they tend to be larger to produce larger currents, we have to have larger transistors, so their parasitic capacitance also tends to be larger and the poles will be further post to lower frequencies. So, the folded cascode has similar parasitic poles as the telescopic

cascode, but dealt into be at lower frequencies, so overall the telescopic cascode will be slower in that. If you have parasitic poles at lower frequencies, you have to push the unity gain frequency to a sufficiently low value, where you have enough phase margin. These are the non dominant poles in ω 's, and then many more of the type of g_m by c_d and so on, but we will have larger parasitic capacitances due to M_9 and M_{10} . First of all there will be additional, and the parasitic capacitance due to M_9 and M_{10} tend to be larger than those of other transistors.

(Refer Slide Time: 17:06)



And the next thing is noise and offset, usually they have similar behavior, so that is why we treat them together, as before we evaluate the output noise of the transistor operating into a voltage source load. Now, just as before the noise from the cascode transistors the node reached the output and noise from the differential pair, as well as the current mirror M_3 and M_4 reach the output in their entirety they will contribute completely to the output noise.

I am not going to work this out again, but please work it out for these individual transistors M_1 and M_2 , M_3 , M_4 , M_5 and M_6 and M_7 and M_8 the arguments are very similar to what we had earlier. Now, in addition to those transistors we also have transistors M_9 and M_{10} , we will see what happens to the noise from those devices. Let us say I have this noise i_{n9} , what happens to it, the incremental current i_{n9} is applied at the input of this common gate amplifier M_5 .

So, I_{n9} flows that way it will get mirrored in this current mirror, so it will flow that way, and it will flow to the output, similarly the noise current of M_{10} I_{n10} , as you can see this is applied to the input of the common gate amplifier M_6 . So, it will go entirely into the current before, because the common gate amplifier or the current buffer presents very low input impedance.

So, you apply a current in the input the same current appears at the output of the current buffer, so I_{n10} appears there, now as usual please do the analysis including g_{ds} and so on. I assumed that there is no g_{ds} at all, so all of this simply appears through M_6 and at the output. Now, the contribution of M_1 for instance can be split into two parts, the part is connected to the tail node will not contribute anything, the part that is connected here, will go through the current mirror and contribute to the output.

So, I will not work out all those things again, but I will just say that the output current will be I_{n1} minus I_{n2} plus I_{n3} minus I_{n4} , this part is exactly the same as before in addition to this, we will also have plus I_{n9} minus I_{n10} . These are due to the current source, which are used to bias the p MOS cascode as well as the current source is used to subtract the bias from the input differential pair, so what is the output noise spectral density is the sum of the spectral density of all these.

(Refer Slide Time: 21:00)

$$i_{n,out} = i_{n1} - i_{n2} + i_{n3} - i_{n4} + i_{n9} - i_{n10}$$

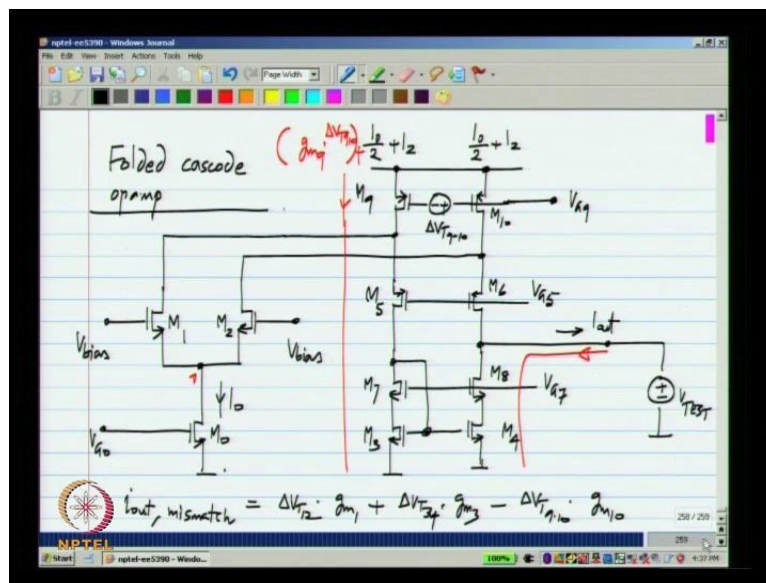
$$S_{i_{n,out}} = \frac{1}{3} kT (g_{m1} + g_{m3} + g_{m9})$$

The spectral density is of these two are identical, these two are identical and those two are identical, we will end up getting 16 by $3 k t g_{m1}$, due to the first pair g_{m3} due to

the second pair g_m due to the third pair. So, first of all there is extra noise, the noise from devices M_9 and M_{10} , also M_9 and M_{10} carry a large current, so they also tend to have a larger g_m .

They carry a larger current than either the differential pair transistors or the other cascode current mirror transistor, so they also have larger noise they tend to have a larger g_m . It is possible to design them with the small g_m , but that needs I over triode voltage and compromise the swing limit, so that is the story with the noise.

(Refer Slide Time: 22:22)



Let us see what happens to offset, again there will be offset between the pairs in M_1 and M_2 , M_3 , M_4 , M_5 , M_6 and 7 and M_8 , and just as before the contributions from the cascode devices M_5 , M_6 , M_7 , M_8 will be 0. And the input pair will contribute completely to the output, and this pair also contribute exactly the same as before, so I will not work it out, but just as practice please do, so the output current due to mismatch.

Is $\Delta V_{T1,2} \times g_{m1}$ $\Delta V_{T1,2}$ is simply being applied at the input of the transistor plus $\Delta V_{T3,4} \times g_{m3}$, it is applied here and comes to the output with the trans conductance. So, g_{m4} which is the same as g_{m3} as usual we have to take care of these extra devices we have to see what happens due to the g_m change, now let us say I have a mismatch between these two transistors.

First of all if there is no mismatch at all this will be biased from a current mirror, such that there is a current $I_{\text{naught 2}} + I_2$ and M_9 , and $I_{\text{naught 2}} + I_2$ in M_{10} . And I will represent the mismatch as though it is acting only on M_9 , it is the mismatch between the two transistors that we are concerned about. Now, you see that the gate voltage of M_{10} is a V_{G9} , and the actual gate voltage M_9 is at $V_{G9} - \Delta v_{t9-10}$, so this of course, as a representation of the changed v_t the difference in v_t between M_9 and M_{10} .

So, what will these two compare to the idle current of $I_{\text{naught 2}} + I_2$, they will be an incremental current, which is given by $g_{M9} \Delta v_{t9-10}$, so that we will get added onto this flowing in the downwards direction. So, what happens to this incremental current the other part remains the same as before, so we will examine only the incremental part of the current.

And that goes into the cascode transistor or common gate amplifier M_5 through the current mirror and comes to the output, in other words it goes here, and then gets mirrored and its run from the output this current equals g_{m9} times Δv_{t9-10} . So, in addition to these contributions we will also have $-\Delta v_{t9-10}$ times g_{m10} , and if we divide the entire result by g_{m1m} and take the variance to get the input referred offset.

(Refer Slide Time: 26:14)

The image shows a handwritten derivation on a digital notepad. The first line defines the input-referred offset as the square root of the output mismatch current divided by the transconductance of the first stage:

$$\text{Input referred offset} : \sqrt{\frac{i_{\text{out, mismatch}}}{g_{m1}}}$$

The second line shows the variance of the offset voltage, $\sigma_{V_{os}}^2$, as the sum of three terms:

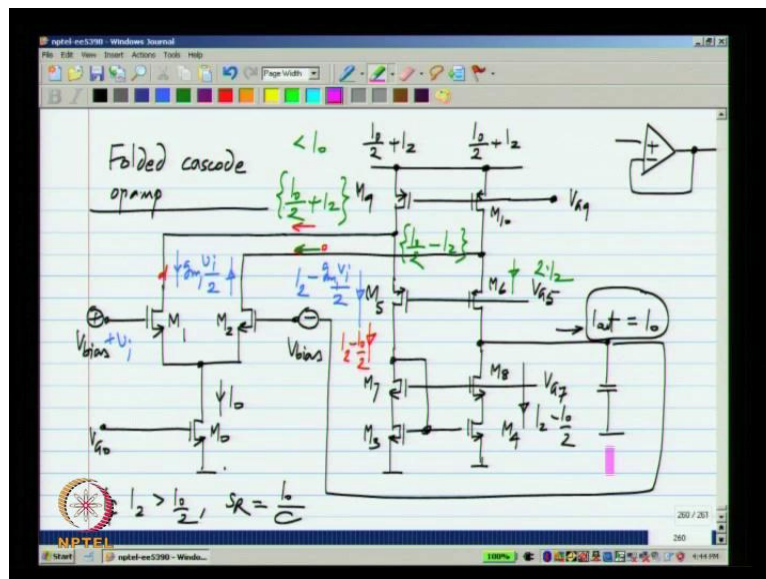
$$\sigma_{V_{os}}^2 = \sigma_{V_{T12}}^2 + \sigma_{V_{T9}}^2 \left(\frac{g_{m9}}{g_{m1}}\right)^2 + \sigma_{V_{T10}}^2 \left(\frac{g_{m10}}{g_{m1}}\right)^2$$

The entire equation is underlined.

The variance of input referred offset is nothing but, this mismatch in duets output current divided by g_{m1} , and the sigma square of that one. What will have is σ_v over square the variance of input referred offset is σ_{vt}^2 square, which appears directly as usual, σ_{vt}^2 square multiplied by g_{m3} by g_{m1} square. And also σ_{vt}^2 square times g_{m10} by g_{m1} square, so just as with noise there is the extra term due to the current source transistors M_9 and M_{10} .

And as before we observe that g_{m9} tends to be large value, because of the larger currents in those transistors, so the contribution of mismatch from the these current sources can be significant. So, what we have got by changing the n MOS cascode devices to p MOS as to extra devices, and they contribute to d c gain they reduce the d c gain, because they contribute to the output conductance. They also increase the value of the input referred noise, and the input referred offset voltage, what other affect do they have, so for that we will calculate the other large signal parameters which are the s quirate and the swing.

(Refer Slide Time: 28:08)



Let us first calculate the quret, I have the opamp and I will assume a unity feedback configuration, though that it is not necessary, this is the minus input terminal I will connect it to the output, basically I am making this amplifier. And I apply input step v_I what happens then, as usual this voltage does not change immediately, so we have an incremental current $g_{m1} v_I$ by 2 going in this direction.

And the current in M 5 would be $I_2 - g_m v_r$, and current in the M 6 would be $I_2 + g_{M1} v_I$ divided by 2, as we go on increasing the value of v_I , this current will go on increasing, but clearly it cannot increase beyond the tail current I_{naught} . So, at some point we will have I_{naught} here, and nothing here that will be just 0, so under those conditions the current here will be $I_2 - I_{naught}$ by 2 this fine, and the current in this arm would be $I_2 + I_{naught}$ by 2.

So, what will be the rate of change of the output, $I_2 - I_{naught}$ by 2 will flow through M 8 and M 4, so what goes to the output will be equal to I_{naught} , so it appears to be exactly the same as before. Now, this makes one particular assumption, this calculation, what we have assume is that this value of I_2 is greater than I_{naught} by 2, so that is what we assume here.

Now, so far we have not made any assumptions about the value of I_2 , now we see that we will get a current of $I_2 - I_{naught}$ by 2 flowing through M 5. Only if I_2 is greater than I_{naught} by 2 if I_2 happen to be less than I_{naught} by 2, nothing will flow here the transistor M 9 will go off into the triode region and nothing will flow through these.

So, if I_2 is greater than I_{naught} by 2, the square root will be I_{naught} divided by c , what happens if I_2 is less than I_{naught} by 2, as you increase the magnitude of v_I at some point this $g_{M1} v_I$ by 2, this current in M 1 will go on increasing. Now, v_I before it reaches a value of I_{naught} , it reaches value of $I_{naught} + I_2$, remember now I_2 is less than I_{naught} by 2.

So, this entire number is less than I_{naught} this current flowing in here is less than I_{naught} , at that point what happens, if you have $I_{naught} + I_2$, and I_{naught} two by I_2 coming here. So, the current in M 5 is 0, and so, the current through this is also 0, let us calculate the current through this part that will be I_{naught} by 2 minus I_2 .

So, the net current flowing through M 6 is the difference of $I_{naught} + I_2$, and I_{naught} by 2 minus I_2 , so what is that that number is simply two times I_2 . And no current is flowing through M 8 and M 4, because this side is off there is no current flowing here either, so two times I_2 will flow into the output capacitor and that will be the maximum rate of change of the output voltage.

(Refer Slide Time: 33:15)

The image shows a digital whiteboard with handwritten mathematical notes. The notes are as follows:

$$\left. \begin{array}{l} \text{If } I_2 > \frac{I_0}{2} : \quad sR = \frac{I_0}{c} ; \\ \text{If } I_2 < \frac{I_0}{2} : \quad sR = \frac{2I_2}{c} ; \end{array} \right\} \frac{\min(I_0, 2I_2)}{c}$$

Below this, it states:

$$I_2 = \frac{I_0}{2} \quad \text{The two limits are equal}$$

Underneath the equation, it is underlined and labeled:

Common choice

So, what we have is if I_2 is greater than I_0 by 2 square root is I_0 by c , and if that is not the case, this square root will be $2 I_0$ by c , and this can be simply written as the minimum value of I_0 , this is I_2 by c . So, minimum value of I_0 and $2 I_0$ divided by c , now this gives you a guideline of how to choose I_2 , we do not like the q rate to be limited to a small value because one current is smaller than the other.

So, the normal choice is to make I_2 to be exactly equal to I_0 by 2, so these two limits will go inside and this is common choice, now earlier I said that M_9 and M_{10} contribute to noise and mismatch an output conductance and so on. Now, because they carry more current than other transistors, they will also have more g_m , so more noise etcetera, etcetera.

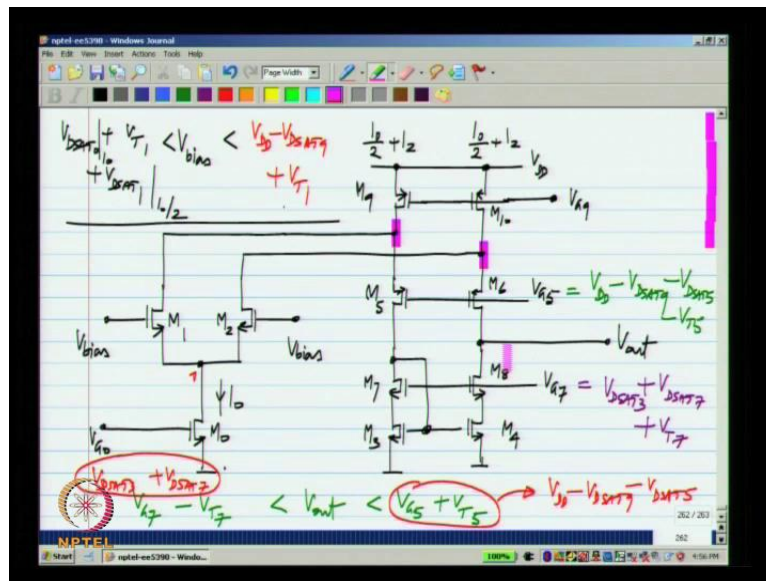
It could try to reduce that by making this I_2 very small that is as small as possible, but if you do that the square root will be severely compromised, the reasonable value of I_2 is to make it equal to I_0 by 2. So, what happens in that condition is that the quiescent current in $M_1, M_2, M_5, M_6, M_7, M_8, M_3, M_4$ will all be equal to I_0 by 2, and the quiescent current here in M_9 and M_{10} will be equal to I_0 .

So, that is the q rate now, so far it look as though this new topology, where we use the p MOS common gate amplifier with n MOS differential pair, has only disadvantages it has more noise more offset more output conductance and so on. It also has more power dissipation, because as you can see the total current is equal to I_0 plus $2 I_2$, we

have extra branches here, so the total current, which was originally I_{naught} is now I_{naught} plus two I_2 .

If you make I_2 equal to $I_{naught} / 2$, we will have a total current of two I_{naught} exactly double, what we had for the simple differential pair as well as the telescopic cascade opamp. So, this topology looks like it has only disadvantages, but there is one aspect in which this is more advantageous compare to the other one, so that is what we will see now and that is the swing limit.

(Refer Slide Time: 36:41)



As before we have a swing limit on the output and swing limit on v_{bias} , what is the limit on v_{bias} , as v_{bias} reduces the transistor M_{naught} gets squeezed, and it will go into the triode region. So, v_{bias} has to be at least equal to the familiar value of $v_{d,sat0}$ plus v_{t1} plus $v_{d,sat1}$, $v_{d,sat1}$ at the current of $I_{naught} / 2$, and $v_{d,sat0}$ at a current of I_{naught} and what is the upper limit.

What happens to the transistors as v_{bias} keeps on increasing, now we see here that these two nodes are bias startup fixed voltage, which is given by V_{GS5} plus v_{hd5} . In the quiescent condition current of I_2 flows through these transistors, and the voltages here is V_{GS5} plus v_{hd5} at a current of I_2 , so that is the drain voltage of M_1 and M_2 .

Now, this v_{bias} can go above that, but not by more than $1 v_t$, so the upper limit on v_{bias} would be V_{GS5} plus v_{hd5} plus v_t , whatever that value is, now what would be

the normal voltage chosen for these points. Now, these transistors M 9 and M 10 must be in saturation, so whatever this voltage is that voltage plus v_{t1} is the limit on a input, so we would like to maximize this voltage. Now, if you take this voltage very close to the supply voltage v_{dd} , what happens is that M 9 and M 10 will enter the triode region we would not want that.

So, these two nodes will be bias that something like $v_{dd} - v_{dsat9}$, at whatever current it is carrying which is $I_{naught} + I_2$. It may be a little lower than this, but you would not make it much lower, because these are fixed current sources and these voltages are also fixed. So, you keep this voltage to be the minimum required, to keep the transistor in saturation region, so in that case the upper limit on v_{bias} will be whatever these voltages plus v_{t1} , so it is $v_{dd} - v_{dsat9} + v_{t1}$.

Now, typically the gate over triode voltages or the saturation voltage v_{dsat} will be of the order of 150 200 or may be three 100 milli volts, and the threshold voltage is at least half a volt even in sub micron technologies. So, you see that this limit is actually more than v_{dd} , so in this particular case the input common mode range can go all the way up to v_{dd} . Now, it depends on the choice of the voltage at the drain of M 9 and M 10, but it can be easily arranged, so that the input common mode range includes the supply voltage v_{dd} .

And what about the output range, if v_{out} goes on reducing it will go below V_{G7} , and if it goes one threshold below V_{G7} M 8 will enter triode region, so the lower limit is $V_{G7} - v_{t8}$. And the upper limit is as it goes on increasing transistor M 6 will enter triode region, if it goes above V_{G5} by one threshold voltage, so the upper limit is $V_{G5} + v_{t5}$.

Now, these limits depend on the choice of V_{G7} and V_{G5} , we would like to minimize V_{G7} and maximize V_{G5} , so that will give us the maximum swing limit. Now, what is the maximum V_{G5} as V_{G5} goes on increasing, the source of M 5 and M 6 also follow V_{G5} , so M 9 and M 10 will enter triode region, if V_{G5} is too high. So, the highest possible value of V_{G5} is v_{dsat9} , so that this transistor is just in saturation plus v_{sd5} , which is $v_{t5} + v_{dsat5}$. If you do adjust this value at the highest value of v_{out} , the highest possible value of v_{out} will be nothing but, this plus v_{t5} .

Now, as V_{G5} goes on increasing the source of $M5$ and $M6$ will go on increasing and $M9$ and $M10$ will enter the triode region, so the highest value is where $M9$ and $M10$ are biased at the edge of triode region, and you have one v_{hd} across $M5$ and $M6$. So, across this we have $v_{d,sat}$ and across, this we have v_{hd} , so the maximum value of V_{G5} is equal to $v_{d,d}$ minus $v_{d,sat9}$ minus v_{hd5} , which is basically $v_{d,sat5}$ minus v_{t5} .

Now, if you set V_{G5} to its highest possible value the upper swing limit, here will be this would be nothing, but $v_{d,d}$ minus $v_{d,sat9}$ minus $v_{d,sat5}$, this is not surprising we have just one $v_{d,sat}$ across $M9$ and $M10$, and $1 v_{d,sat}$ across $M6$. So, this can go within $2 v_{d,sat}$ of $v_{d,d}$, similarly what is the lowest value of V_{G7} , when V_{G7} reduces the source of $M7$ and $M8$ hold down, and if they become too small $M3$ and $M4$ will enter triode region.

So, the smallest value of V_{G7} would be to accommodate $v_{d,sat}$ across this and V_{G8} of $M8$, so that will be $v_{d,sat3}$ plus v_{sd7} , which is $v_{d,sat7}$ plus v_{t7} . Now, if I substitute that over here what do I get I will have $v_{d,sat3}$ plus $v_{d,sat7}$, so just like on upper side all I have to do is to leave $1 v_{d,sat}$ for $M4$ and $1 v_{d,sat}$ for $M8$.

(Refer Slide Time: 45:20)

Folded cascode opamp swing limits:

$$V_{DSAT10} + V_{DSAT1} + V_{T1} < V_{in,cm} < V_{G5} + V_{DSAT5} + V_{T1}$$

$$\{V_{D0} - V_{DSAT7} + V_{T1}\}$$

$$V_{G7} - V_{T7} < V_{out} < V_{G5} + V_{T5}$$

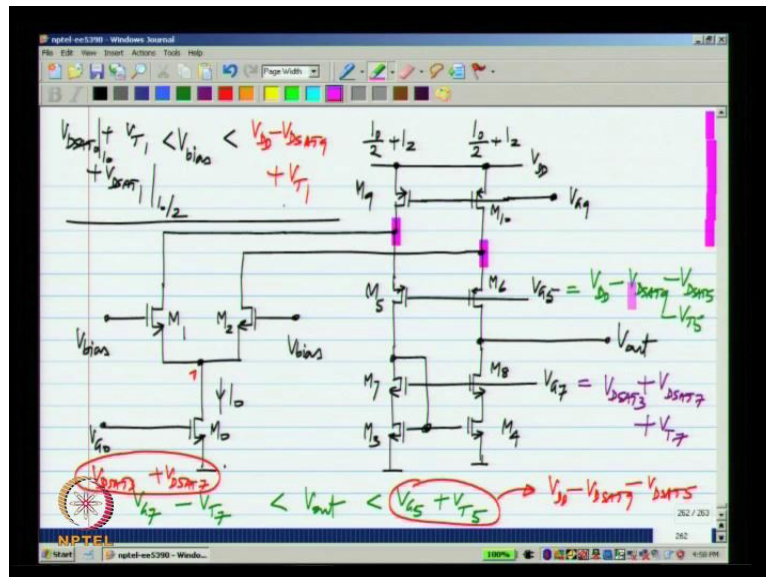
$$\{V_{DSAT3} + V_{DSAT7}\} \quad \{V_{D0} - V_{DSAT7} - V_{DSAT6}\}$$

So, it can also come within two saturation voltages of the lower rail and ground, so swing limits of the folded cascode opamp are given by this is the range for the input common mode voltage. And this can be a maximum of $v_{d,d}$ minus $v_{d,sat9}$ plus v_{t1} the lower limit is the same, as it is always been $v_{d,sat0}$ plus $v_{d,sat1}$ plus v_{t1} .

And the output voltage has a limit of $V_{G5} + v_{t5}$, and here $V_{G7} - v_{t7}$ and with the optimum values of V_{G5} and V_{G7} will have $v_{d sat 3} + v_{d sat 7}$ on the lower side. And $v_{d d} - v_{d sat 9} - v_{d sat 5}$ on the upper side, so the output can go with in two $v_{d sat}$ supplies. And this is the advantage of the telescopic cascode opamp the swing limits are a lot higher than in the differential pair, and also in the telescopic cascode opamp.

To the folded cascode opamp has a lot higher swing limit, and that is why it is used in many cases where the signals swing is important. And also another important to note is that in the telescopic cascode opamp, unlike in the other cases the input is applied to some devices and the output node is from a different device.

(Refer Slide Time: 47:24)



So, the constants on the input and output are more independent in this case than in the simple differential pair or the telescopic cascode, what we have done, so far is to analyze single stage opamps. What are known as single stage opamps, these are called single stage opamp, because there is a single trans conductor g_m . As you recall the expression for trans conductance for all these three opamps that differential pair, telescopic and folded cascode g_m , what is different is the output resistance and that gives you different value of $d c$ gain.

Now the details of noise and offset are bi and large similar in the three opamps, except that in the folded cascode, you have extra devices, so you have extra noise and offset.

Now, the telescopic and folded the cascode opamps give you higher d c gain, that is why they are popular, and finally if you really want a high swing you go for the folded cascode, because it gives you the high swing that is possible.

Now, the square root is similar for all three opamps and because the telescopic and folded cascodes have more nodes compare to differential pair. They also have a more parasitic poles and 0's and this limits their speed to lower value compare to the differential pair. That is if you have more parasitic poles, you need to make sure that you are unity gain frequency is low enough, your integrator is, so, enough, so that in spite of all those parasitic delays you are stable.

That is your phase margin is sufficient, so that is a quick summary of single stage opamp, now we know that single stage of opamps are not very useful, when you have resistive loads, because they have some trans conductance g_m . And the telescopic and folded cascode have higher output resistance, but let us say we load all these three opamp with the given load resistance r_l , which happens to be much smaller than the output resistance of the opamps.

Then all three will give same d c gain, so it is only with the capacitive load, that the telescopic cascode and folded cascode opamps give you higher gain than the differential pair. If you put a resistive load, and a typical resistive load as lower value, than the output resistance of transistors, all three will give equal gain and that is not useful. In order to have high d c gain with the resistive load, as we have discussed earlier, when we discuss the opamp at the control source level, we have to go to two stages.

So, instead of converting the output of the trans conductor into a voltage by passing, it through a capacitor directly. We should use a current controlled voltage source stage, the second stage across which we connect the integrating capacitor c and form the 2 stage opamp, and we will discuss the details of that in the next lecture.

Thank you.